

**Low hysteresis and large room temperature magnetocaloric effect of Gd<sub>5</sub>Si<sub>2.05</sub>- x Ge<sub>1.95</sub>- x Ni<sub>2x</sub> (2x = 0.08, 0.1) alloys**

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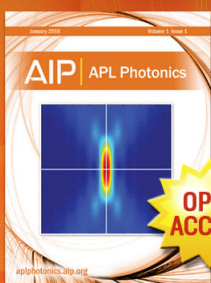
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# Low hysteresis and large room temperature magnetocaloric effect of $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$ ( $2x = 0.08, 0.1$ ) alloys

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$\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys were prepared by arc melting followed by annealing at 1273 K for 96 h. Mixed monoclinic  $\text{Gd}_5\text{Si}_2\text{Ge}_2$ -type phase, orthorhombic  $\text{Gd}_5\text{Si}_4$ -type phase, and a small amount of  $\text{Gd}_5\text{Si}_3$ -type phase were obtained in these alloys.  $\text{Gd}_5\text{Si}_{2.01}\text{Ge}_{1.91}\text{Ni}_{0.08}$  alloy undergoes a second-order transition ( $T_C$ ) around 300 K, whereas  $\text{Gd}_5\text{Si}_2\text{Ge}_{1.9}\text{Ni}_{0.1}$  alloy exhibits two transitions including a first-order transition ( $T_C^{\text{II}}$ ) at  $\sim 295$  K and second-order transition ( $T_C^{\text{I}}$ ) at  $\sim 301$  K. Ni substitution can effectively reduce the thermal hysteresis and magnetic hysteresis while maintaining large magnetic entropy change. The maximum magnetic entropy changes ( $|\Delta S_M^{\text{max}}|$ ) of  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  alloys with  $2x = 0.08$  and  $0.1$  are  $4.4$  and  $5.0 \text{ J kg}^{-1} \text{ K}^{-1}$ , respectively, for  $0-2 \text{ T}$ , and are  $8.0$  and  $9.1 \text{ J kg}^{-1} \text{ K}^{-1}$ , respectively, for  $0-5 \text{ T}$ . Low hysteresis performance and relatively large magnetic entropy change make these alloys favorable for magnetic refrigeration applications. © 2013 American Institute of Physics. [<http://dx.doi.org/10.1063/1.4795434>]

## I. INTRODUCTION

As an energy-saving, efficient and eco-friendly cooling technology, magnetic refrigeration is receiving more and more global attention.<sup>1</sup> Various materials<sup>2-7</sup> have been investigated regarding to their applications in this new cooling technology. In particular, discovery of the giant magnetocaloric effect (GMCE) in the  $\text{Gd}_5(\text{Si}_2\text{Ge}_2)$  and  $\text{Gd}_5(\text{Si}_x\text{Ge}_{1-x})_4$  ( $0.24 \leq x \leq 0.5$ ) alloys<sup>2,8</sup> is a benchmark in the study of magnetic refrigerants near room temperature. However,  $\text{Gd}_5(\text{Si}_2\text{Ge}_2)$  exhibits large hysteretic loss in the temperature range between 270 and 300 K, which reduces its potential cooling efficiency.<sup>9</sup> As reported earlier, a small amount (total of 0.33 at. %) of Fe, Co, Ni, or Cu substitution for Si and Ge in the  $\text{Gd}_5\text{Ge}_2\text{Si}_2$  alloy have significant impact on the maximum value of the magnetic entropy change ( $\Delta S_M$ ) and the Curie temperature ( $T_C$ ).<sup>10</sup> Among the different 3d metal substitutions, Ni was the one providing the most promising results, as it increases the transition temperature and did not decrease much  $\Delta S_M$ . Shull and his coworkers found that the addition of Cu, Ga, Mn, and Al completely eliminated the hysteresis loss presented in the undoped  $\text{Gd}_5\text{Ge}_2\text{Si}_2$  alloy between 270 and 330 K, broadened the magnetic entropy change ( $\Delta S_M$ ) peak, and shifted its peak position from 275 to 305 K, similar to that observed earlier for  $\text{Gd}_5\text{Ge}_{1.9}\text{Si}_2\text{Fe}_{0.1}$ .<sup>11,12</sup> However, in the case of doping the same amount of either Sn or Bi, a negligible effect on the magnetocaloric properties was evident.<sup>11</sup> Recent results show that partial substitution of Nb in  $\text{Gd}_5\text{Si}_{2-x}\text{Ge}_{2-x}\text{Nb}_{2x}$  alloys increased

$T_C$  to  $\sim 295$  K and enhanced the magnetocaloric effect as  $x$  increased to  $x = 0.05$ . The  $\Delta S_M = -9.6 \text{ J kg}^{-1} \text{ K}^{-1}$  for  $\Delta H = 2 \text{ T}$  was obtained, which is  $\sim 50\%$  higher than that of Nb-free alloy. And microstructure examination indicated that a low amount of detrimental  $\text{Gd}_5\text{Si}_3$  phase was precipitated.<sup>13</sup> As far as Ni doping is concerned, most previous work focused on the alloy with very low Ni concentrations, typically less than 0.03 at. %.<sup>10</sup> In the present work,  $\text{Gd}_5\text{Si}_{2.05}\text{Ge}_{1.95}$  based alloys doped with slightly higher Ni contents were prepared. Their hysteresis behavior, structure, and magnetocaloric properties were investigated.

## II. EXPERIMENTS

The alloys with nominal composition of  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08$  and  $0.1$ ) were prepared by arc melting the raw materials of Gd, Si, Ge, and Ni with purities higher than 99.95 wt. % under argon atmosphere. The ingots were re-melted several times to ensure the composition homogeneity. As-cast ingots were sealed in a quartz tube and annealed at 1273 K for 96 h and subsequently quenched in water. The structural characterization was performed by the X-ray diffractometer (XRD) with Cu-K $\alpha$  radiation. Magnetic measurements were carried out using a Quantum Design Physical Property Measurement System (model PPMS-9).

## III. RESULTS AND DISCUSSION

Fig. 1 shows the XRD patterns for the  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys. Three types of phases, i.e., monoclinic  $\text{Gd}_5\text{Si}_2\text{Ge}_2$ -type phase, orthorhombic  $\text{Gd}_5\text{Si}_4$ -type phase, and hexagonal  $\text{Gd}_5(\text{Si,Ge})_3$ -type phase, were observed. The XRD peaks at  $\sim 26.2^\circ$  and  $37.9^\circ$

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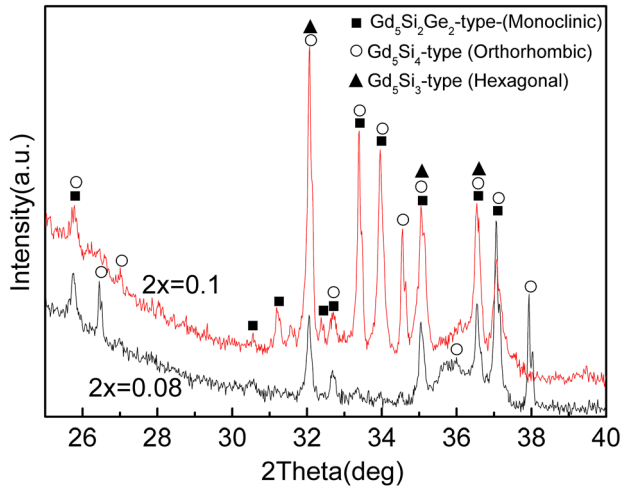


FIG. 1. The XRD patterns for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys at room temperature.

corresponding to 5:4-type phase were present on the pattern of  $2x = 0.08$  sample, but absent on that of  $2x = 0.1$  sample. The XRD peaks at  $\sim 31.2^\circ$  and  $32.4^\circ$  correspond to the monoclinic  $\text{Gd}_5\text{Si}_2\text{Ge}_2$ -type phase. The result also indicates that the content of Ni-substitution has an effect on the formation of 5-2-2 phase. With increasing Ni content from  $\sim 0.89$  ( $2x = 0.08$ ) to  $\sim 1.11$  at. % ( $2x = 0.1$ ), the amount of orthorhombic  $\text{Gd}_5\text{Si}_4$ -type phase decreases and the amount of monoclinic  $\text{Gd}_5\text{Si}_2\text{Ge}_2$ -type phase increases. The XRD peaks at  $\sim 35.2^\circ$  and  $\sim 36.6^\circ$  in Fig. 1 are related to the hexagonal  $\text{Gd}_5(\text{Si, Ge})_3$ -type phase.

The temperature dependencies of magnetization for the  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys measured in an applied field of 0.05 T between 5 and 300 K under field cooling (FC) and field heating (FH) conditions are shown in Fig. 2. The  $T_C$  was defined as the temperature at the maximum of  $|dM/dT|$  vs  $T$  plot based on FH curve. The lack of thermal hysteresis in  $\text{Gd}_5\text{Si}_{2.01}\text{Ge}_{1.91}\text{Ni}_{0.08}$  alloy indicates that it should undergo a second-order magnetic transition, and  $T_C$  is around 300 K. For  $\text{Gd}_5\text{Si}_2\text{Ge}_{1.9}\text{Ni}_{0.1}$ , two slopes are observed in  $M$ - $T$  curves, indicating two magnetic transitions,

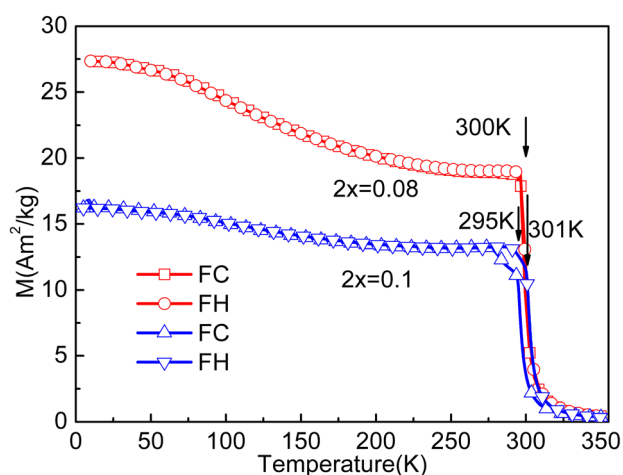


FIG. 2. Magnetization-temperature curves for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys measured in a magnetic field of 0.05 T.

a first-order transition ( $T_C^{\text{II}}$ ) at  $\sim 295$  K and a second-order transition ( $T_C^{\text{I}}$ ) at  $\sim 301$  K. It is also found that the thermal hysteresis between FC and FH curves is negligible for  $2x = 0.08$  alloy, whereas that is  $\sim 6$ – $13$  K for  $2x = 0.1$ . A similar behavior was observed for the magnetic hysteresis in the magnetic isotherms for the experimental alloys, as will be discussed later.

Figure 3 displays the isothermal magnetization curves for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) alloys. The  $\text{Gd}_5\text{Si}_2\text{Ge}_{1.9}\text{Ni}_{0.1}$  alloy (Fig. 3(b)) has the typical magnetization characteristics of pure  $\text{Gd}_5\text{Si}_2\text{Ge}_2$  for the temperatures above  $T_C^{\text{I}}$  ( $\sim 301$  K). We can see a typical field induced transition from the PM to the field-induced ferromagnetic state. Combined with partial magnetic hysteresis with respect to a reversed magnetic field, this shows that the transitions are first order. The transition occurs at higher field values with increasing temperature in the range between 288 K and 324 K. As already stated, it has been hypothesized that this transition is the result of a field-induced first-order crystallographic phase change from the paramagnetic monoclinic phase to a ferromagnetic orthorhombic phase,<sup>14</sup> which results in the peak of  $(-\Delta S_M)$  for  $\text{Gd}_5\text{Si}_2\text{Ge}_{1.9}\text{Ni}_{0.1}$  alloy shifting  $\sim 290$  K at low field ( $\Delta\mu_0 H = 2.0$  T) to  $\sim 300$  K at high field ( $\Delta\mu_0 H = 5.0$  T) (shown in Fig. 4). The  $\text{Gd}_5\text{Si}_{2.01}\text{Ge}_{1.91}\text{Ni}_{0.08}$  alloy (Fig. 3(a)),

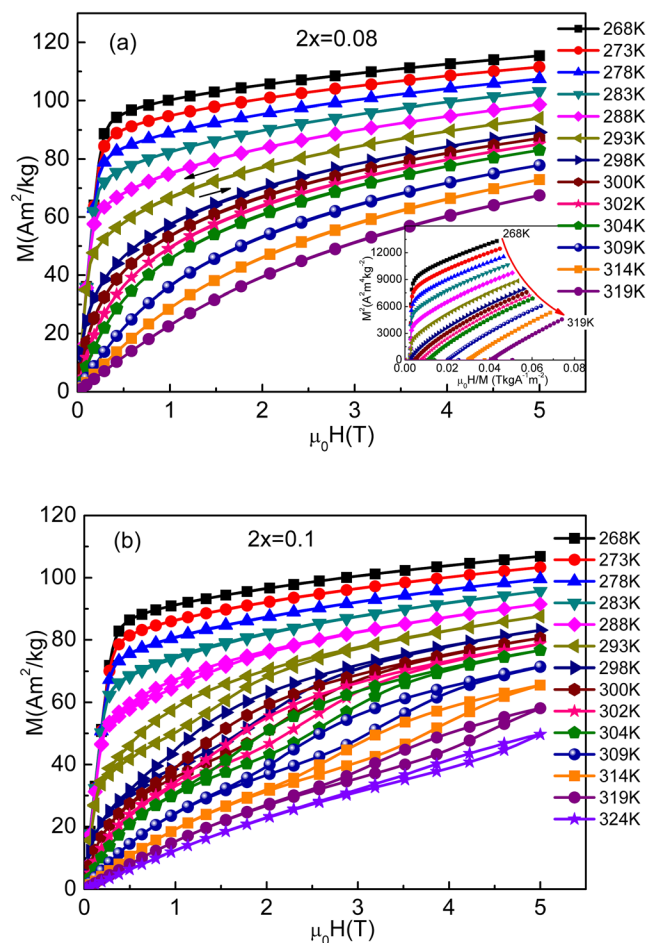


FIG. 3. Field dependencies of magnetization of  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x = 0.08, 0.1$ ) compounds measured with increasing field and decreasing field in maximum fields up to 5 T. The inset of the lower right corner of Fig. 3(a) shows the Arrott plots of the  $\text{Gd}_5\text{Si}_{2.01}\text{Ge}_{1.91}\text{Ni}_{0.08}$  alloy.

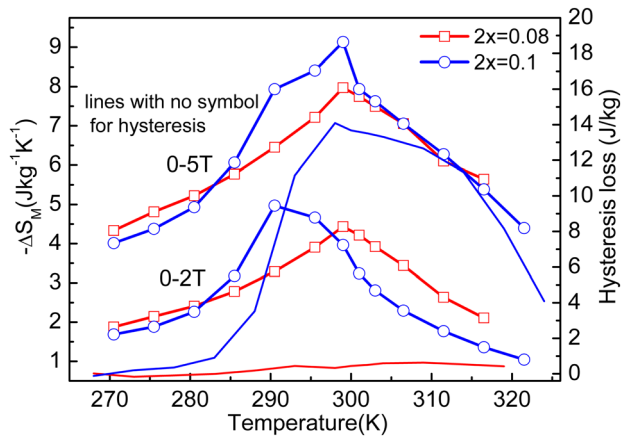


FIG. 4. Temperature dependencies of magnetic entropy change and hysteresis loss for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x=0.08, 0.1$ ) compounds. Hysteresis loss is plotted for the magnetic-field change from 0 to 5 T.

however, has lost the two-step magnetic ordering and shows negligible hysteresis, and it performs as a typical ferromagnet. The Arrott plots of the  $\text{Gd}_5\text{Si}_{2.01}\text{Ge}_{1.91}\text{Ni}_{0.08}$  alloy are displayed in the inset of Fig. 3(a). No inflection or negative slope is observed as an indication that FM–PM transition is of second-order.<sup>15,16</sup>

The magnetic-entropy changes ( $-\Delta S_M$ ) were calculated based on the magnetic isotherms in the vicinity of  $T_C$  using the Maxwell relation. The ( $-\Delta S_M$ ) vs  $T$  plots of the  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  alloys are presented in Fig. 4. The maximum magnetic entropy change ( $|\Delta S_M^{\text{max}}|$ ) for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  with  $2x=0.08$  and  $0.1$  is  $4.4$  and  $5.0 \text{ J kg}^{-1} \text{ K}^{-1}$ , respectively, for the applied-field change of 0 to 2 T. The  $|\Delta S_M^{\text{max}}|$  is  $8.0$  and  $9.1 \text{ J kg}^{-1} \text{ K}^{-1}$ , respectively, for 0 to 5 T. These values are comparable to that of pure Gd ( $5.1 \text{ J kg}^{-1} \text{ K}^{-1}$  at  $\Delta\mu_0 H=2.0 \text{ T}$  and  $10.2 \text{ J kg}^{-1} \text{ K}^{-1}$  at  $\Delta\mu_0 H=5.0 \text{ T}$ ). Refrigerant capacity (RC) as another effective criterion for characterizing the refrigerant efficiency could be estimated by the method of Gschneidner.<sup>17</sup> When the applied field changed from 0 to 2 T, RC values of  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  with  $2x=0.08$  and  $0.1$  are  $122$  and  $90 \text{ J kg}^{-1}$ , respectively. The RC value under an applied field change of 5 T for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x=0.1$ ) alloy is  $288 \text{ J kg}^{-1}$ , which is slightly smaller than that of  $\text{Gd}_5\text{Si}_2\text{Ge}_2$  ( $305 \text{ J kg}^{-1}$ ,  $\Delta\mu_0 H=5.0 \text{ T}$ ).<sup>12</sup> One way to take into account the hysteresis loss of each alloy is to simply subtract it from the corresponding RC value.<sup>12</sup> From Fig. 4, the value of magnetic hysteresis loss for  $2x=0.08$  compound is calculated as less than  $1 \text{ J/kg}$  and the maximum magnetic hysteresis loss for  $2x=0.1$  alloy is about  $14 \text{ J/kg}$ . Both values are much smaller than that of the  $\text{Gd}_5\text{Si}_2\text{Ge}_2$  (average value is about  $65 \text{ J/kg}$ ). The low hysteresis with relatively large magnetic entropy change for  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  ( $2x=0.08, 0.1$ ) alloys is favorable for the applications of magnetic refrigeration materials.

#### IV. CONCLUSIONS

Ni substituted  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  alloys ( $2x=0.08$  and  $0.1$ ) exhibit multiphase structure. The Curie temperature for second order transition of the alloys with  $2x=0.08$  and

$0.1$  is  $300$  and  $301 \text{ K}$ , respectively. An obvious first order transition is exhibited around  $295 \text{ K}$  for  $2x=0.1$  compound. The maximum of magnetic entropy change ( $|\Delta S_M^{\text{max}}|$ ) of  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  alloys with  $2x=0.08$  and  $0.1$  is  $4.4$  and  $5.0 \text{ J kg}^{-1} \text{ K}^{-1}$ ,  $8.0$  and  $9.1 \text{ J kg}^{-1} \text{ K}^{-1}$ , respectively, under an applied field changes from 0 to 2 T and 0 to 5 T, respectively. The thermal and magnetic hysteresis behaviors are negligible in  $2x=0.08$  alloy. Though thermal hysteresis is  $\sim 6\text{--}13 \text{ K}$  for the alloy with  $2x=0.1$ , the maximum magnetic hysteresis loss is only about  $14 \text{ J/kg}$  around transition temperature. This study extends the range of Ni doping in  $\text{GdSiGeX}$ , as well as focuses on compositions with Si:Ge ratios larger than one, which can be beneficial for magnetic refrigeration applications. Low hysteresis and large  $\Delta S_M$  suggest that  $\text{Gd}_5\text{Si}_{2.05-x}\text{Ge}_{1.95-x}\text{Ni}_{2x}$  alloys ( $2x=0.08$  and  $0.1$ ) be good candidates for magnetocaloric materials working at room temperature.

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